



Fast Recovery Diodes (Hockey PUK Version), 920/1050 A



DO-200AB (B-PUK)

FEATURES

- High power fast recovery diode series
- 2.0 μ s to 3.0 μ s recovery time
- High voltage ratings up to 3000 V
- High current capability
- Optimized turn-on and turn-off characteristics
- Low forward recovery
- Fast and soft reverse recovery
- Press PUK encapsulation
- Case style conform to JEDEC® DO-200AB (B-PUK)
- Maximum junction temperature 150 °C
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT

PRODUCT SUMMARY

$I_{F(AV)}$	920 A to 1050 A
Package	DO-200AB (B-PUK)
Circuit configuration	Single Diode

TYPICAL APPLICATIONS

- Snubber diode for GTO
- High voltage freewheeling diode
- Fast recovery rectifier applications

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	SD1053C..L		UNITS
		S20	S30	
$I_{F(AV)}$		1050	920	A
	T_{hs}	55	55	°C
$I_{F(RMS)}$		1940	1700	A
I_{FSM}	50 Hz	15 000	13 000	
	60 Hz	15 700	13 610	
V_{RRM}	Range	1800 to 2500	1800 to 3000	V
t_{rr}		2.0	3.0	μ s
	T_J	25		°C
T_J	-40 to 150			

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	V_{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-SD1053C..S20L	18	1800	1900	50
	22	2200	2300	
	25	2500	2600	
VS-SD1053C..S30L	18	1800	1900	
	22	2200	2300	
	25	2500	2600	
	28	2800	2900	
	30	3000	3100	



FORWARD CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS		SD1053C..L		UNITS
				S20	S30	
Maximum average forward current at heatsink temperature	$I_{F(AV)}$	180° conduction, half sine wave Double side (single side) cooled		1050 (450)	920 (390)	A
				55 (85)	55 (85)	°C
Maximum RMS forward current	$I_{F(RMS)}$	25 °C heatsink temperature double side cooled		1940	1700	
Maximum peak, one-cycle forward, non-repetitive surge current	I_{FSM}	t = 10 ms t = 8.3 ms t = 10 ms t = 8.3 ms	No voltage reappplied 100 % V_{RRM} reappplied Sinusoidal half wave, initial $T_J = T_J$ maximum	15 000	13 000	A
				15 700	13 610	
				12 620	10 930	
				13 210	11 450	
Maximum I^2t for fusing	I^2t	t = 10 ms t = 8.3 ms t = 10 ms t = 8.3 ms	No voltage reappplied 100 % V_{RRM} reappplied	1125	845	kA ² s
				1027	772	
				796	598	
				727	546	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reappplied		11 250	8450	kA ² √s
Low level value of threshold voltage	$V_{F(TO)1}$	(16.7 % $\times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)}$, $T_J = T_J$ maximum)		1.34	1.51	V
High level value of threshold voltage	$V_{F(TO)2}$	(I > $\pi \times I_{F(AV)}$, $T_J = T_J$ maximum)		1.48	1.67	
Low level value of forward slope resistance	r_{f1}	(16.7 % $\times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)}$, $T_J = T_J$ maximum)		0.37	0.50	mΩ
High level value of forward slope resistance	r_{f2}	(I > $\pi \times I_{F(AV)}$, $T_J = T_J$ maximum)		0.33	0.45	
Maximum forward voltage drop	V_{FM}	$I_{pk} = 1500$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sinusoidal wave		1.90	2.26	V

RECOVERY CHARACTERISTICS								
CODE	MAXIMUM VALUE AT $T_J = 25$ °C	TEST CONDITIONS			TYPICAL VALUES AT $T_J = 150$ °C			
	t_{rr} AT 25 % I_{RRM} (μs)	I_{pk} SQUARE PULSE (A)	dI/dt (A/μs)	V_r (V)	t_{rr} AT 25 % I_{RRM} (μs)	Q_{rr} (μC)	I_{rr} (A)	
S20	2.0	1000	100	- 50	4.0	400	180	
S30	3.0				4.5	550	230	

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating and storage temperature range	T_J, T_{Stg}		-40 to 150	°C
Maximum thermal resistance, case junction to heatsink	R_{thJ-hs}	DC operation single side cooled	0.073	K/W
		DC operation double side cooled	0.031	
Mounting force, ± 10 %			14 700 (1500)	N (kg)
Approximate weight			255	g
Case style		See dimensions - link at the end of datasheet	DO-200AB (B-PUK)	

ΔR_{thJ-hs} CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE		
180°	0.009	0.008	0.006	0.006	$T_J = T_J$ maximum	K/W
120°	0.011	0.011	0.011	0.011		
90°	0.014	0.014	0.015	0.015		
60°	0.020	0.021	0.021	0.022		
30°	0.036	0.036	0.036	0.036		

Note

- The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

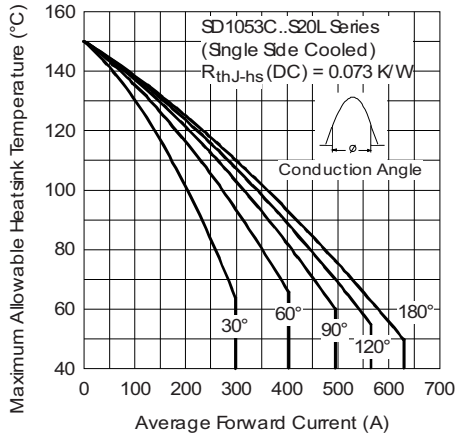


Fig. 1 - Current Ratings Characteristics

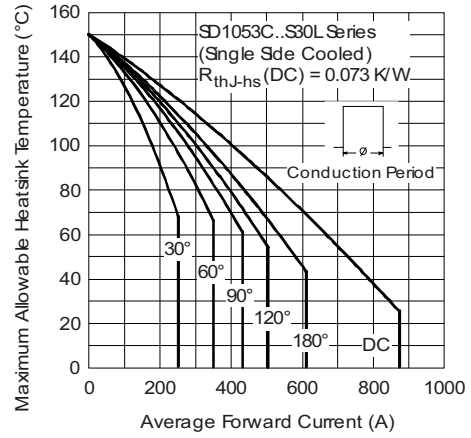


Fig. 4 - Current Ratings Characteristics

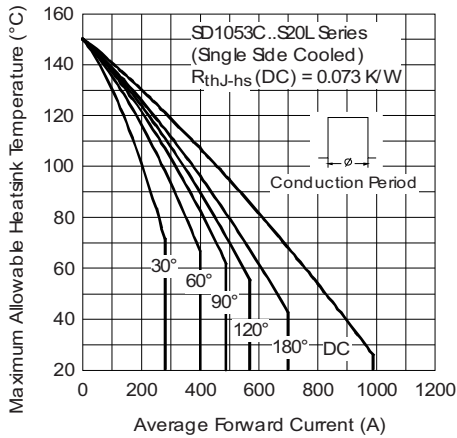


Fig. 2 - Current Ratings Characteristics

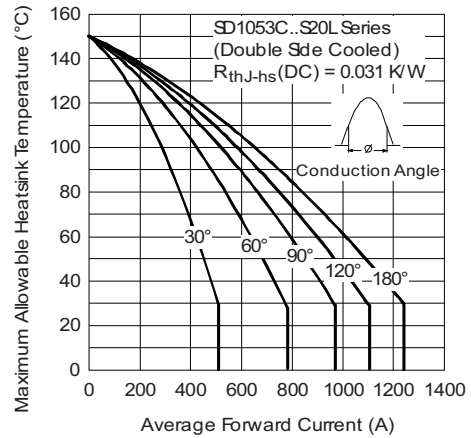


Fig. 5 - Current Ratings Characteristics

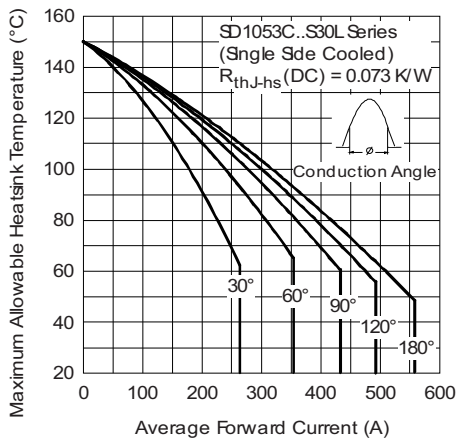


Fig. 3 - Current Ratings Characteristics

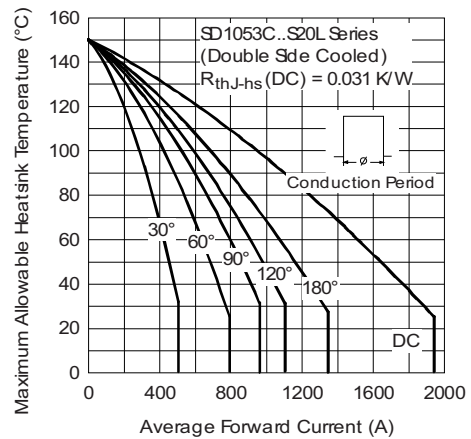


Fig. 6 - Current Ratings Characteristics

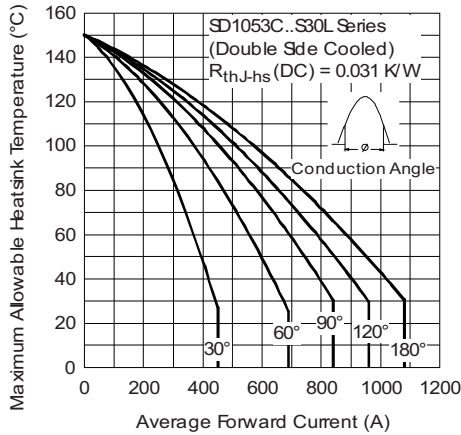


Fig. 7 - Current Ratings Characteristics

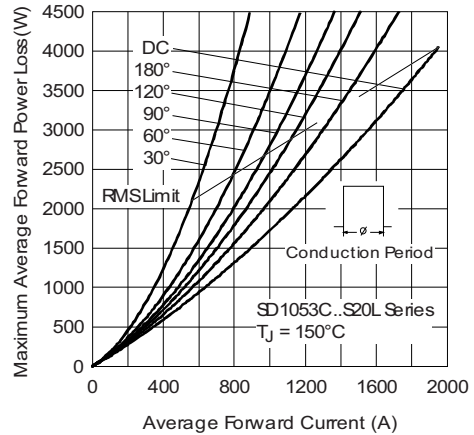


Fig. 10 - Forward Power Loss Characteristics

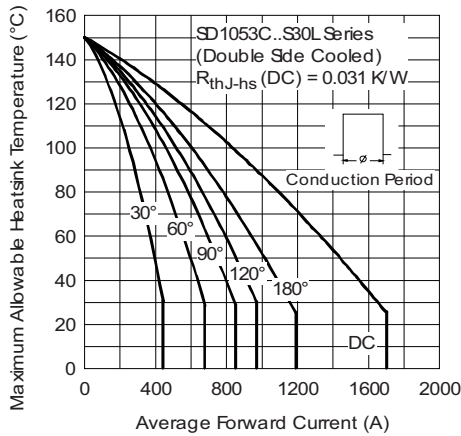


Fig. 8 - Current Ratings Characteristics

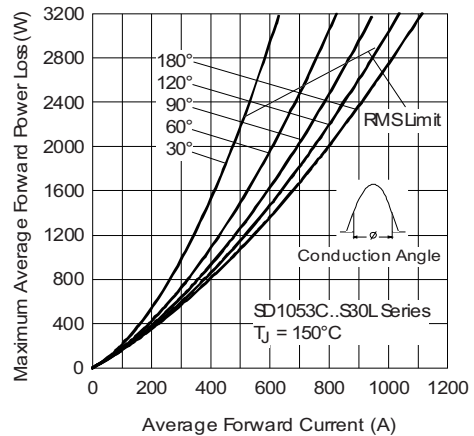


Fig. 11 - Forward Power Loss Characteristics

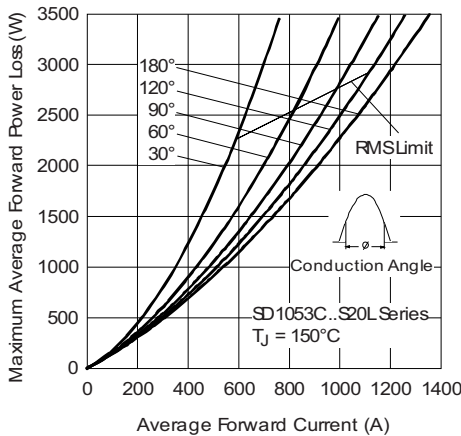


Fig. 9 - Forward Power Loss Characteristics

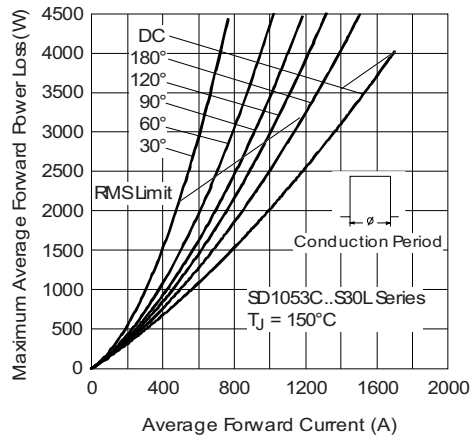


Fig. 12 - Forward Power Loss Characteristics

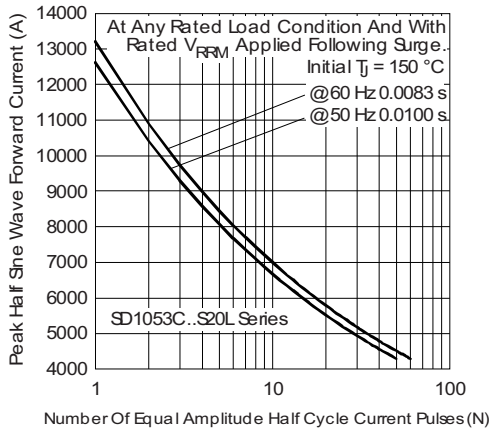


Fig. 13 - Maximum Non-Repetitive Surge Current

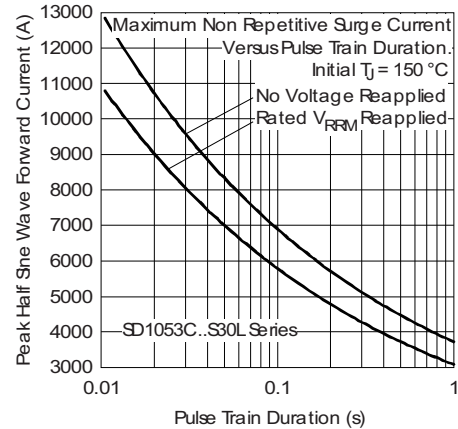


Fig. 16 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

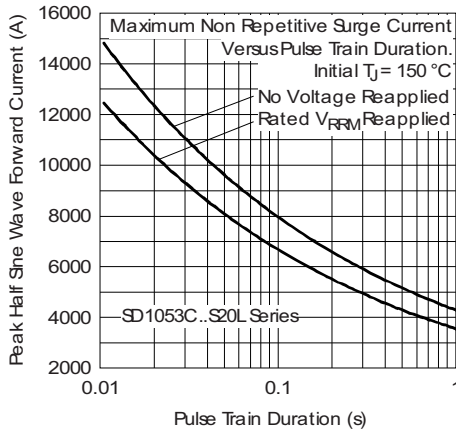


Fig. 14 - Maximum Non-Repetitive Surge Current

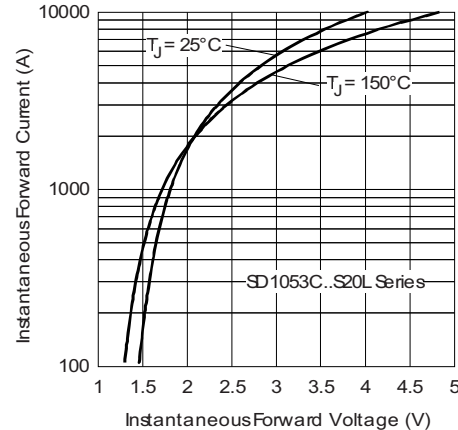


Fig. 17 - Forward Voltage Drop Characteristics

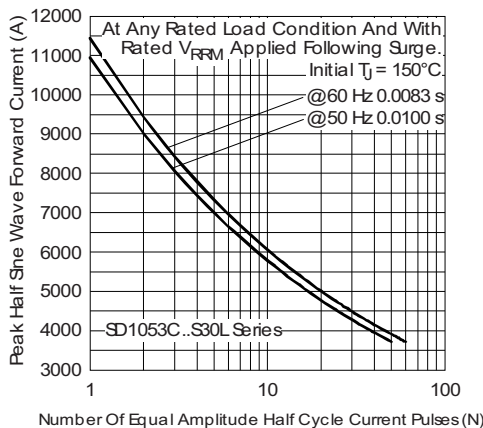


Fig. 15 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

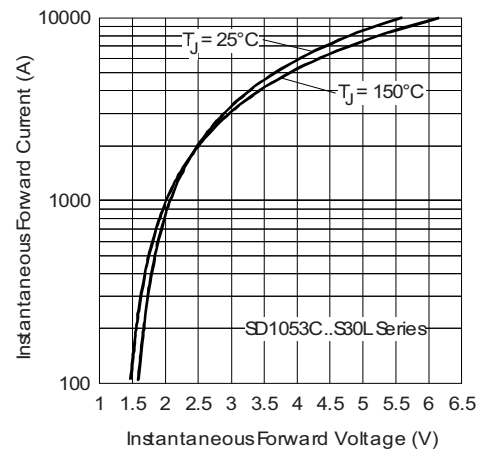


Fig. 18 - Forward Voltage Drop Characteristics

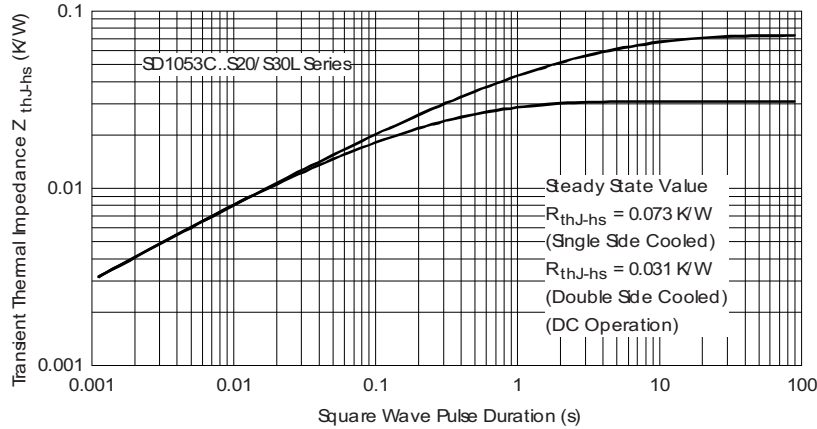


Fig. 19 - Thermal Impedance Z_{thJ-hs} Characteristic

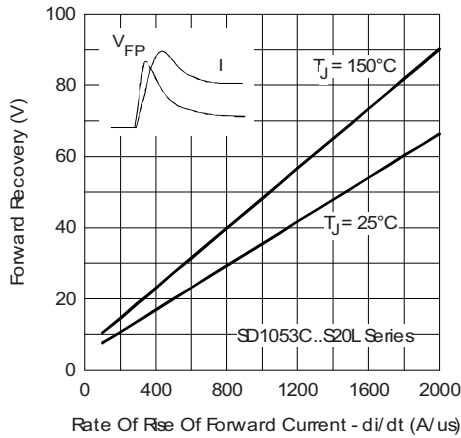


Fig. 20 - Typical Forward Recovery Characteristics

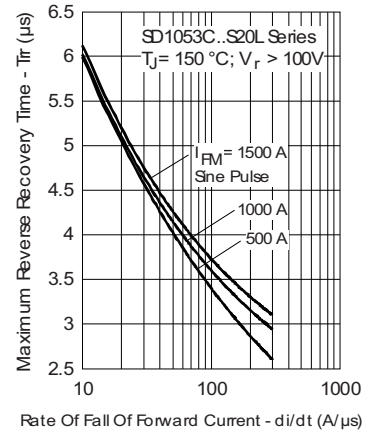


Fig. 22 - Recovery Time Characteristics



Fig. 21 - Typical Forward Recovery Characteristics

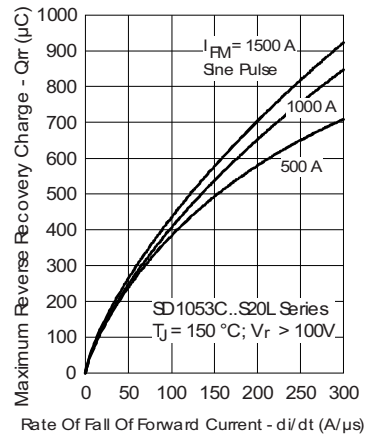


Fig. 23 - Recovery Charge Characteristics

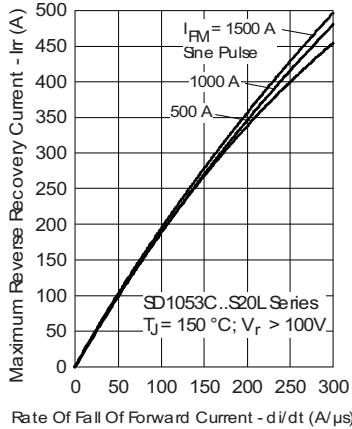


Fig. 24 - Recovery Current Characteristics

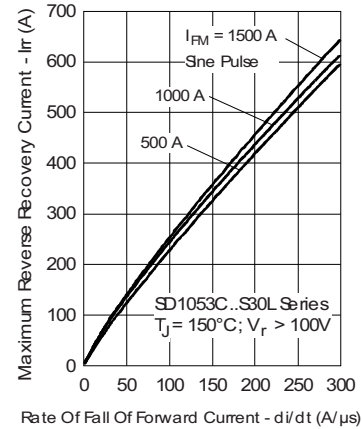


Fig. 27 - Recovery Current Characteristics

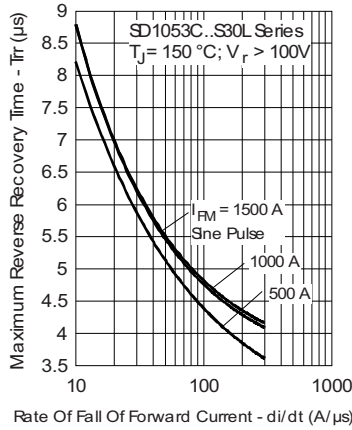


Fig. 25 - Recovery Time Characteristics

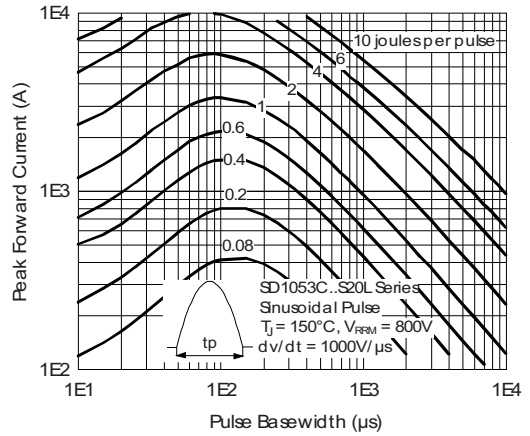


Fig. 28 - Maximum Total Energy Loss Per Pulse Characteristics



Fig. 26 - Recovery Charge Characteristics

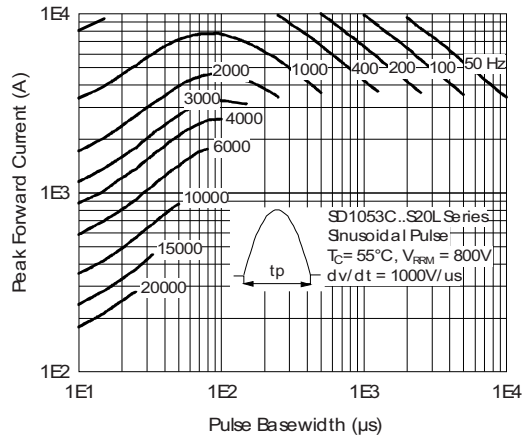


Fig. 29 - Frequency Characteristics

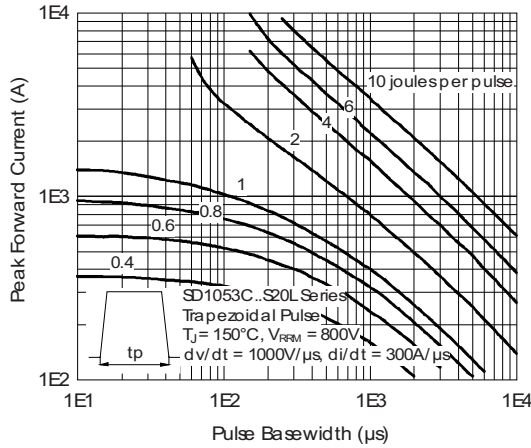


Fig. 30 - Maximum Total Energy Loss Per Pulse Characteristics

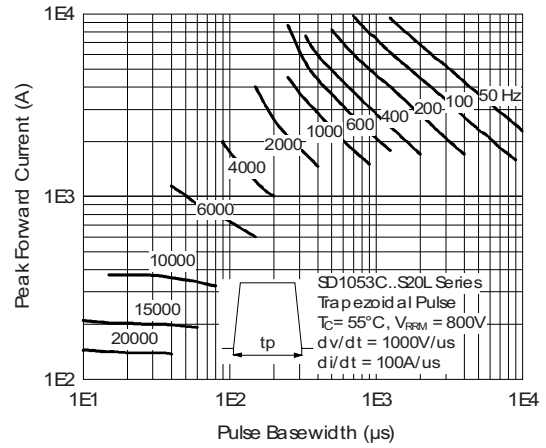


Fig. 33 - Frequency Characteristics

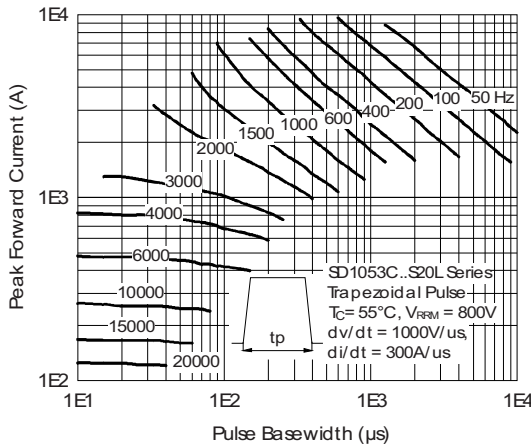


Fig. 31 - Frequency Characteristics

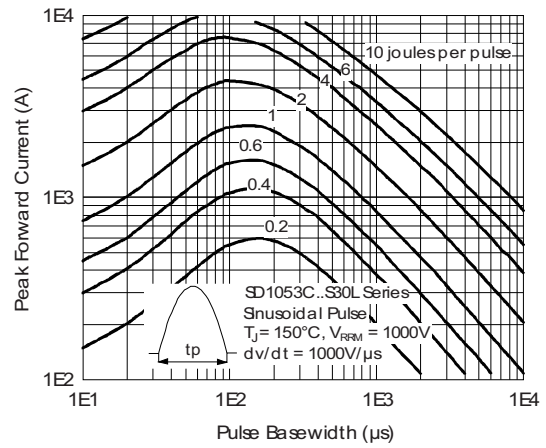


Fig. 34 - Maximum Total Energy Loss Per Pulse Characteristics

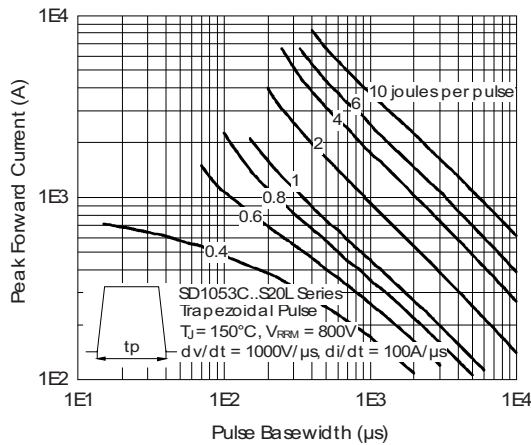


Fig. 32 - Maximum Total Energy Loss Per Pulse Characteristics

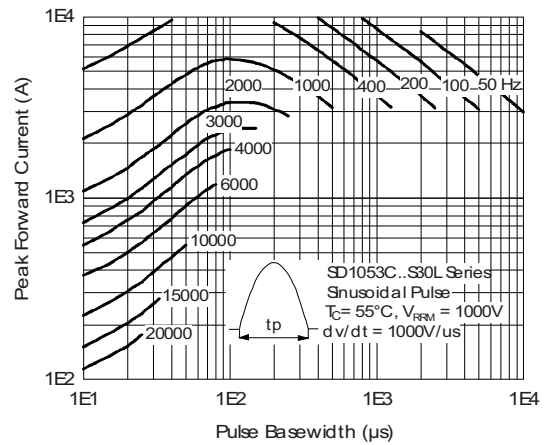


Fig. 35 - Frequency Characteristics

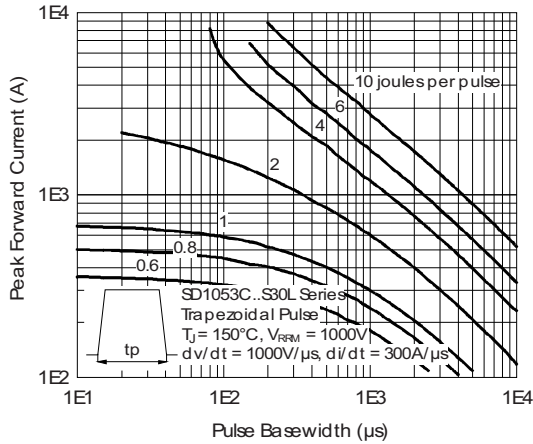


Fig. 36 - Maximum Total Energy Loss Per Pulse Characteristics

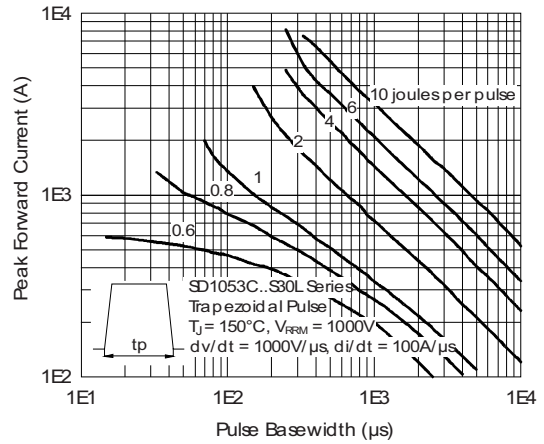


Fig. 38 - Maximum Total Energy Loss Per Pulse Characteristics

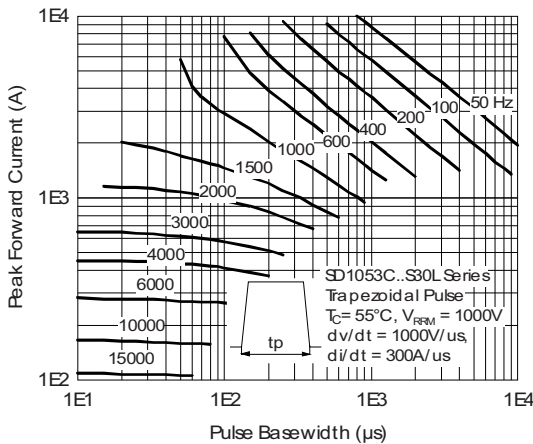


Fig. 37 - Frequency Characteristics



Fig. 39 - Frequency Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	SD	105	3	C	30	S30	L
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- ①
- ②
- ③
- ④
- ⑤
- ⑥
- ⑦
- ⑧

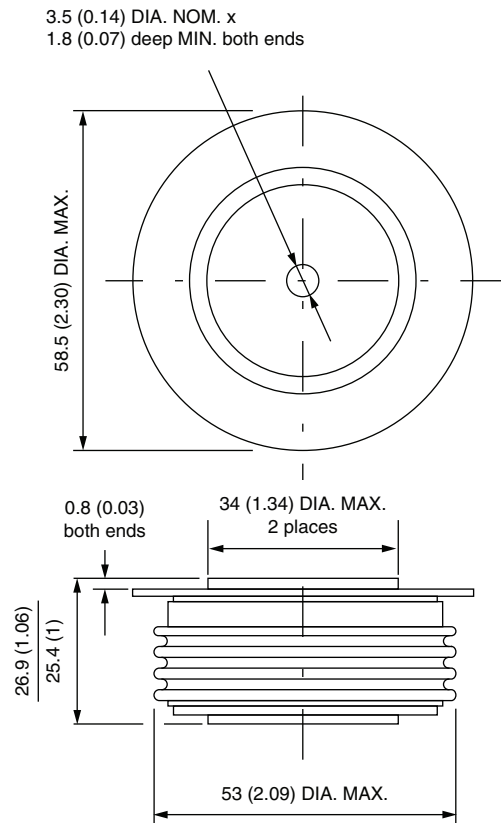
- 1** - Vishay Semiconductors product
- 2** - Diode
- 3** - Essential part number
- 4** - 3 = Fast recovery
- 5** - C = Ceramic PUK
- 6** - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- 7** - t_{tr} code
- 8** - L = PUK case DO-200AB (B-PUK)

LINKS TO RELATED DOCUMENTS

Dimensions	www.vishay.com/doc?95246
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DO-200AB (B-PUK)

DIMENSIONS in millimeters (inches)



Quote between upper and lower pole pieces has to be considered after application of mounting force (see Thermal and Mechanical Specifications)



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